

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of) ATOMIC LAYER DEPOSITION
Hwang et al.) METHOD AND SEMICONDUCTOR
Application No.) DEVICE FABRICATING
Filing Date:) APPARATUS HAVING ROTATABLE
) GAS INJECTORS
) Group Art Unit:
) Examiner:

Commissioner for Patents
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AMENDMENTS**AMENDMENT TO THE CLAIMS:**

Please cancel claims 4-14 which were allowed in the parent application.

Please prosecute claims 1-3 in this application.

LISTING OF CLAIMS:

1. (previously presented) An atomic layer deposition method comprising:
respectively loading a plurality of substrates into a plurality of reaction cells, the plurality of reaction cells being disposed in a reaction chamber; and
alternately and repeatedly applying various vapor substances onto each substrate such that a thin film is formed on each substrate, wherein a plurality of vapor injection pipes each injecting one of the vapor substances periodically scans over each substrate to apply the various vapor substances alternately and repeatedly onto each substrate.
2. (previously presented) The method of claim 1, wherein each substrate is heated using a heater disposed in the reaction chamber.
3. (previously presented) The method of claim 1, wherein RF power is applied to the vapor injection pipes such that plasma is generated in the reaction chamber.

4. (canceled)
5. (canceled)
6. (canceled)
7. (canceled)
8. (canceled)
9. (canceled)
10. (canceled)
11. (canceled)
12. (canceled)
13. (canceled)
14. (canceled)